

CMOS Low Voltage 2.5Ω Dual SPDT Switch

ADG736L

FEATURES

1.8 V to 5.5 V single supply 2.5 Ω (typical) on resistance Low on-resistance flatness Guaranteed leakage performance over -40°C to $+85^{\circ}\text{C}$ -3 dB bandwidth > 200 MHz Rail-to-rail operation 10-lead MSOP package Fast switching times t_{ON} 16 ns

ton 1011s

Typical power consumption (<0.01 μW)
TTL/CMOS compatible

APPLICATIONS

USB 1.1 signal switching circuits
Cell phones
PDAs
Battery-powered systems
Communication systems
Sample-and-hold systems
Audio signal routing
Audio and video switching
Mechanical reed relay replacement

GENERAL DESCRIPTION

The ADG736L is a monolithic device comprising two independently selectable CMOS single pole, double throw (SPDT) switches. The switches are designed using a submicron process that provides low power dissipation, yet gives high switching speed, low on resistance, low leakage currents, and wide input signal bandwidth.

The on resistance profile is very flat over the full analog signal range. This ensures excellent linearity and low distortion when switching audio signals. Fast switching speed also makes the part suitable for video signal switching.

The ADG736L operates from a single 1.8 V to 5.5 V supply, making it ideally suited to portable and battery-powered instruments.

Each switch conducts equally well in both directions when on; each has an input signal range that extends to the power supplies. The ADG736L exhibits break-before-make switching action.

The ADG736L is available in a 10-lead MSOP.

FUNCTIONAL BLOCK DIAGRAM

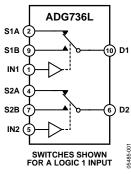


Figure 1.

PRODUCT HIGHLIGHTS

- 1. 1.8 V to 5.5 V Single-Supply Operation.
- 2. Guaranteed Leakage Performance.
- 3. Very Low R_{ON} (4.5 Ω Maximum at 5 V, 8 Ω Maximum at 3 V).
- 4. Low On Resistance Flatness.
- 5. -3 dB Bandwidth > 200 MHz.
- 6. Low Power Dissipation.

Rev. 0

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ADG736L* Product Page Quick Links

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Comparable Parts

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Evaluation Kits <a> □

• Evaluation Board for 10-Lead MSOP Devices in the Switches and Multiplexers Portfolio

Documentation <a>□

Data Sheet

• ADG736L: CMOS Low Voltage 2.5 Ω Dual SPDT Switch Data Sheet

User Guides

 UG-1037: Evaluation Board for 10-Lead MSOP Devices in the Switches and Multiplexers Portfolio

Reference Materials

Product Selection Guide

· Switches and Multiplexers Product Selection Guide

Design Resources -

- ADG736L Material Declaration
- PCN-PDN Information
- Quality And Reliability
- · Symbols and Footprints

Discussions <a>□

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TABLE OF CONTENTS

Features	1
Applications	. 1
General Description	. 1
Functional Block Diagram	1
Product Highlights	1
Revision History	2
Specifications	3
Absolute Maximum Ratings	. 5
FSD Caution	5

Pin Configuration and Function Descriptions	6
Typical Performance Characteristics	7
Test Circuits	9
Terminology	10
Applications Information	11
Outline Dimensions	12
Ordering Guide	12

REVISION HISTORY

1/07—Revision 0: Initial Version

SPECIFICATIONS

 V_{DD} = 5 V \pm 10%, GND = 0 V; all specifications -40°C to +85°C, unless otherwise noted.

Table 1.

	В\	B Version ¹		
		−40°C to		
Parameter	25°C	+85°C	Unit	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range		$0 V to V_{DD}$	V	
On Resistance (R _{ON})	2.5		Ω typ	$V_S = 0 \text{ V to } V_{DD}$, $I_{DS} = -10 \text{ mA}$; see Figure 10
	4	4.5	Ω max	
On Resistance Match Between Channels (ΔR_{ON})	0.1		Ω typ	$V_S = 0 \text{ V to } V_{DD}, I_{DS} = -10 \text{ mA}$
		0.4	Ω max	
On Resistance Flatness (R _{FLAT (ON)})	0.5		Ω typ	$V_S = 0 \text{ V to } V_{DD}, I_{DS} = -10 \text{ mA}$
		1.2	Ω max	
LEAKAGE CURRENTS				$V_{DD} = 5.5 \text{ V}$
Source Off Leakage Is (OFF)	±0.01		nA typ	$V_S = 4.5 \text{ V/1 V}, V_D = 1 \text{ V/4.5 V}; \text{ see Figure 11}$
	±0.1	±0.3	nA max	
Channel On Leakage ID, Is (ON)	±0.01		nA typ	$V_S = V_D = 1 \text{ V or } 4.5 \text{ V; see Figure } 12$
3 · · ·	±0.1	±0.3	nA max	
DIGITAL INPUTS				
Input High Voltage, V _{INH}		2.4	V min	
Input Low Voltage, V _{INL}		0.8	V max	
Input Current, I _{INL} or I _{INH}				
•	0.005		μA typ	V _{IN} = V _{INL} or V _{INH}
		±0.1	μA max	
DYNAMIC CHARACTERISTICS ²				
ton	12		ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
		16	ns max	$V_S = 3 V$; see Figure 13
t _{OFF}	5		ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
		8	ns max	$V_s = 3 \text{ V}$; see Figure 13
Break-Before-Make Time Delay, t _D	7		ns typ	$R_L = 300 \Omega, C_L = 35 pF$
, -		1	ns min	$V_{S1} = V_{S2} = 3 \text{ V}$; see Figure 14
Off Isolation	-62		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$
	-82		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 15
Channel-to-Channel Crosstalk	-62		dB typ	$R_L = 50 \Omega$, $C_L = 5 \text{ pF}$, $f = 10 \text{ MHz}$
Charlifer to-Charlifer Crosstain	-82 -82		dB typ	$R_L = 50 \Omega$, $C_L = 5 \text{ pF}$, $f = 1 \text{ MHz}$; see Figure 16
Pandwidth (2 dP)	200			$R_L = 50 \Omega$, $C_L = 5 \text{ pF}$, $T = 1 \text{ MHz}$; see Figure 10 $R_L = 50 \Omega$, $C_L = 5 \text{ pF}$; see Figure 17
Bandwidth (–3 dB)			MHz typ	N _L = 30 12, C _L = 3 pr, see rigure 17
C ₅ (OFF)	9		pF typ	
C _D , C _s (ON) POWER REQUIREMENTS	32		pF typ	V _{DD} = 5.5 V
	0.001		A +	
I_{DD}	0.001	1.0	μA typ	Digital inputs = 0 V or 5 V
	Ī	1.0	μA max	

 $^{^1}$ Temperature range is -40°C to $+85^\circ\text{C}$ for the B version. 2 Guaranteed by design; not subject to production test.

 V_{DD} = 3 V \pm 10%, GND = 0 V. All specifications –40°C to +85°C, unless otherwise noted.

Table 2.

	B Version ¹			
		−40°C to		
Parameter	25°C	+85°C	Unit	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range		$0 V to V_{DD}$	V	
On Resistance (R _{ON})	5	5.5	Ωtyp	$V_S = 0 \text{ V to } V_{DD}$, $I_{DS} = -10 \text{ mA}$; see Figure 10
		8	Ω max	
On Resistance Match Between Channels (ΔR_{ON})	0.1		Ωtyp	$V_S = 0 \text{ V to } V_{DD}, I_{DS} = -10 \text{ mA}$
		0.4	Ω max	
On Resistance Flatness (R _{FLAT (ON)})		2.5	Ωtyp	$V_S = 0 \text{ V to } V_{DD}$, $I_{DS} = -10 \text{ mA}$
LEAKAGE CURRENTS				$V_{DD} = 3.3 \text{ V}$
Source Off Leakage Is (OFF)	±0.01		nA typ	$V_S = 3 \text{ V}/1 \text{ V}, V_D = 1 \text{ V}/3 \text{ V}; \text{ see Figure 11}$
	±0.1	±0.3	nA max	
Channel On Leakage ID, Is (ON)	±0.01		nA typ	$V_S = V_D = 1 \text{ V or } 3 \text{ V}$; see Figure 12
	±0.1	±0.3	nA max	
DIGITAL INPUTS				
Input High Voltage, V _{INH}		2.0	V min	
Input Low Voltage, V _{INL}		0.4	V max	
Input Current, I _{INL} or I _{INH}				
	0.005		μA typ	$V_{IN} = V_{INL} \text{ or } V_{INH}$
		±0.1	μA max	
DYNAMIC CHARACTERISTICS ²				
ton	14		ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
		20	ns max	$V_s = 2 V$; see Figure 13
toff	6		ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
		10	ns max	$V_S = 2 V$; see Figure 13
Break-Before-Make Time Delay, t _D	7		ns typ	$R_L = 300 \Omega$, $C_L = 35 pF$
		1	ns min	$V_{S1} = V_{S2} = 2 \text{ V}$; see Figure 14
Off Isolation	-62		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$
	-82		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 15
Channel-to-Channel Crosstalk	-62		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$
	-82		dB typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$; see Figure 16
Bandwidth (–3 dB)	200		MHz typ	$R_L = 50 \Omega$, $C_L = 5 pF$; see Figure 17
C _s (OFF)	9		pF typ	, , , , , , ,
C _D , C _S (ON)	32		pF typ	
POWER REQUIREMENTS			1	$V_{DD} = 3.3 \text{ V}$
I_{DD}	0.001		μA typ	Digital inputs = 0 V or 3 V
		1.0	μA max	

 $^{^1}$ Temperature range is -40°C to $+85^\circ\text{C}$ for the B version. 2 Guaranteed by design; not subject to production test.

ABSOLUTE MAXIMUM RATINGS

 $T_A = 25$ °C, unless otherwise noted.

Table 3.

Table 3.	
Parameter	Rating
V _{DD} to GND	-0.3 V to +6 V
Analog, Digital Inputs ¹	$-0.3 \text{ V to V}_{DD} + 0.3 \text{ V or } 30 \text{ mA},$ whichever occurs first
Continuous Current, S or D	30 mA
Peak Current, S or D	100 mA (Pulsed at 1 ms, 10% duty cycle maximum)
Operating Temperature Range	
Industrial (B Version)	-40°C to +85°C
Storage Temperature Range	−65°C to +150°C
Junction Temperature	150°C
MSOP Package, Power Dissipation	315 mW
θ_{JA} Thermal Impedance	205°C/W
Lead Temperature (Soldering, 10 sec)	300°C
IR Reflow (Peak Temperature, <20 sec)	235°C
Lead-Free Reflow	
Peak Temperature	260(+0/-5)°C
Time at Peak Temperature	10 sec to 40 sec
ESD	2 kV

 $^{^{\}rm 1}$ Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Only one absolute maximum rating may be applied at any one time.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

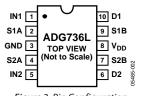


Figure 2. Pin Configuration

Table 4. Pin Function Descriptions

Pin No.	Mnemonic	Description
1	IN1	Logic Control Input.
2	S1A	Source Terminal. May be an input or an output.
3	GND	Ground (0 V) Reference.
4	S2A	Source Terminal. May be an input or an output.
5	IN2	Logic Control Input.
6	D2	Drain Terminal. May be an input or an output.
7	S2B	Source Terminal. May be an input or an output.
8	V _{DD}	Most Positive Power Supply Potential.
9	S1B	Source Terminal. May be an input or an output.
10	D1	Drain Terminal. May be an input or an output.

Table 5. Truth Table

Logic	Switch A	Switch B
0	Off	On
_ 1	On	Off

TYPICAL PERFORMANCE CHARACTERISTICS

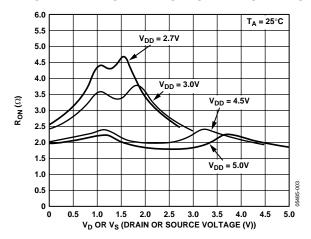


Figure 3. On Resistance as a Function of V_D (V_S) Single Supplies

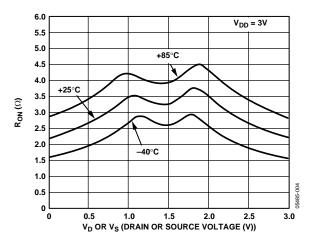


Figure 4. On Resistance as a Function of V_D (V_S) for Different Temperatures V_{DD} = 3 V

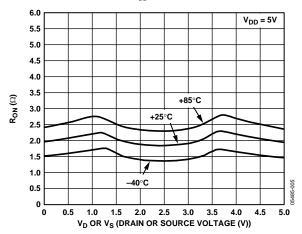


Figure 5. On Resistance as a Function of V_D (V_S) for Different Temperatures $V_{DD} = 5 \text{ V}$

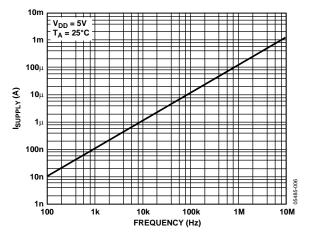


Figure 6. Supply Current vs. Input Switching Frequency

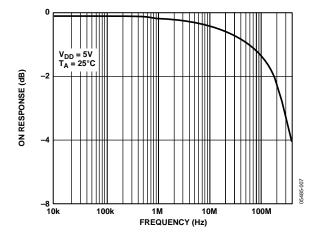


Figure 7. Bandwidth

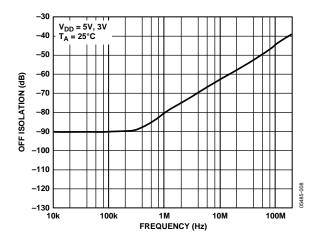


Figure 8. Off Isolation vs. Frequency

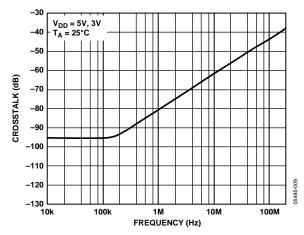


Figure 9. Crosstalk vs. Frequency

TEST CIRCUITS

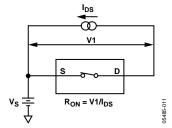


Figure 10. On Resistance

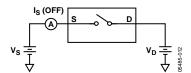


Figure 11. Off Leakage

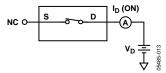


Figure 12. On Leakage

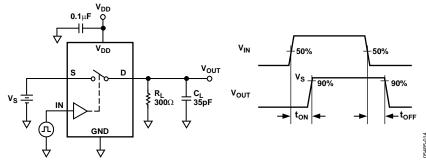


Figure 13. Switching Times

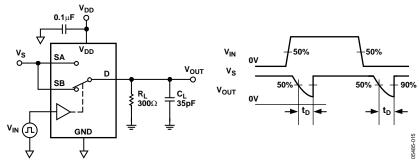


Figure 14. Break-Before-Make Time Delay, t_D

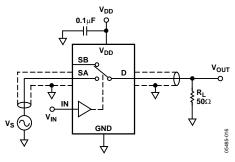


Figure 15. Off Isolation

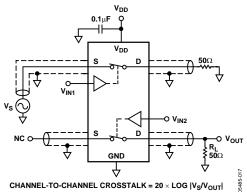


Figure 16. Channel-to-Channel Crosstalk

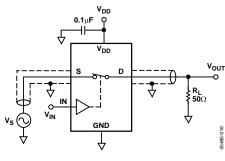


Figure 17. Bandwidth

TERMINOLOGY

Ron

Ohmic resistance between D and S.

$\Delta R_{\rm ON}$

On resistance match between any two channels, such as $R_{\rm ON}$ maximum – $R_{\rm ON}$ minimum.

R_{FLAT} (ON)

Flatness is defined as the difference between the maximum and minimum value of on resistance as measured over the specified analog signal range.

Is (OFF)

Source leakage current with the switch off.

I_D , I_S (ON)

Channel leakage current with the switch on.

$V_D(V_S)$

Analog voltage on Terminal D and Terminal S.

Cs (OFF)

Off switch source capacitance.

C_D , C_S (ON)

On switch capacitance.

ton

Delay between applying the digital control input and the output switching on (see Figure 13).

toff

Delay between applying the digital control input and the output switching off.

\mathbf{t}_{D}

Off time or on time measured between the 90% points of both switches, when switching from one address state to another (see Figure 14).

Crosstalk

A measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.

Off Isolation

A measure of unwanted signal coupling through an off switch.

Bandwidth

The frequency at which the output is attenuated by -3 dB.

On Response

The frequency response of the on switch.

On Loss

The voltage drop across the on switch, seen on the On Response vs. Frequency plot (see Figure 7) as how many decibels the signal is away from 0 dB at very low frequencies.

APPLICATIONS INFORMATION

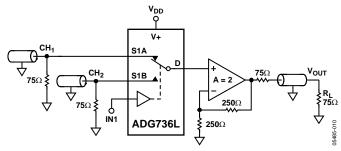
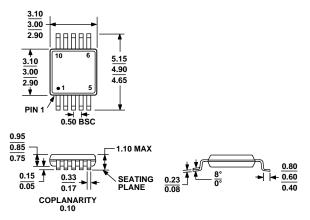


Figure 18. Using the ADG736L to Select Between Two Video Signals

OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MO-187-BA

Figure 19. 10-Lead Mini Small Outline Package [MSOP] (RM-10) Dimensions shown in millimeters

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option	Branding
ADG736LBRM	−40°C to +85°C	10-Lead Mini Small Outline Package (MSOP)	RM-10	SOY
ADG736LBRM-REEL	−40°C to +85°C	10-Lead Mini Small Outline Package (MSOP)	RM-10	SOY
ADG736LBRM-REEL7	−40°C to +85°C	10-Lead Mini Small Outline Package (MSOP)	RM-10	SOY
ADG736LBRMZ ¹	−40°C to +85°C	10-Lead Mini Small Outline Package (MSOP)	RM-10	SOZ
ADG736LBRMZ-REEL ¹	−40°C to +85°C	10-Lead Mini Small Outline Package (MSOP)	RM-10	SOZ
ADG736LBRMZ-REEL7 ¹	−40°C to +85°C	10-Lead Mini Small Outline Package (MSOP)	RM-10	SOZ

 $^{^{1}}$ Z = Pb-free part.



Rev. 0 | Page 12 of 12